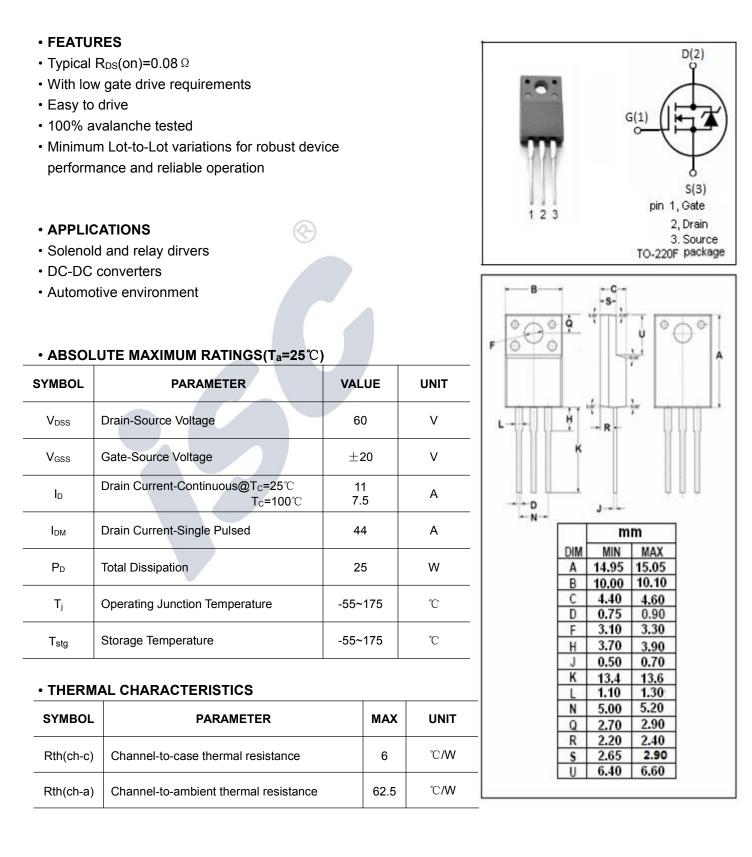


## **INCHANGE SEMICONDUCTOR**

## **Isc N-Channel MOSFET Transistor**

## STP60NF06FP



1



# **Isc N-Channel MOSFET Transistor**

# STP60NF06FP

### **ELECTRICAL CHARACTERISTICS**

#### $T_{C}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	60			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =±20V; I <sub>D</sub> =0.25mA	24			V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =8A		80	100	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 60V; V <sub>GS</sub> = 0V; T <sub>J</sub> =25°C T <sub>J</sub> =125°C			1 10	μA
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =16A, V <sub>GS</sub> = 0 V			1.3	v



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2